

# HVC359

## Variable Capacitance Diode for VCXO

# HITACHI

 Rev. 0  
 Nov. 1995

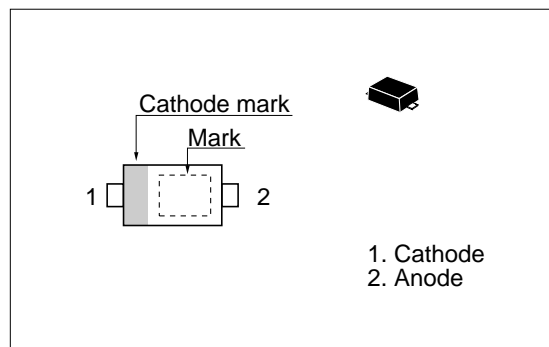
### Features

- High capacitance ratio and good C-V linearity.
- To be usable at low voltage.
- Ultra small Flat Package (UFP) is suitable for surface mount design.

### Ordering Information

Type No.	Laser Mark	Package Code
HVC359	S	UFP

### Outline



### Absolute Maximum Ratings (Ta = 25°C)

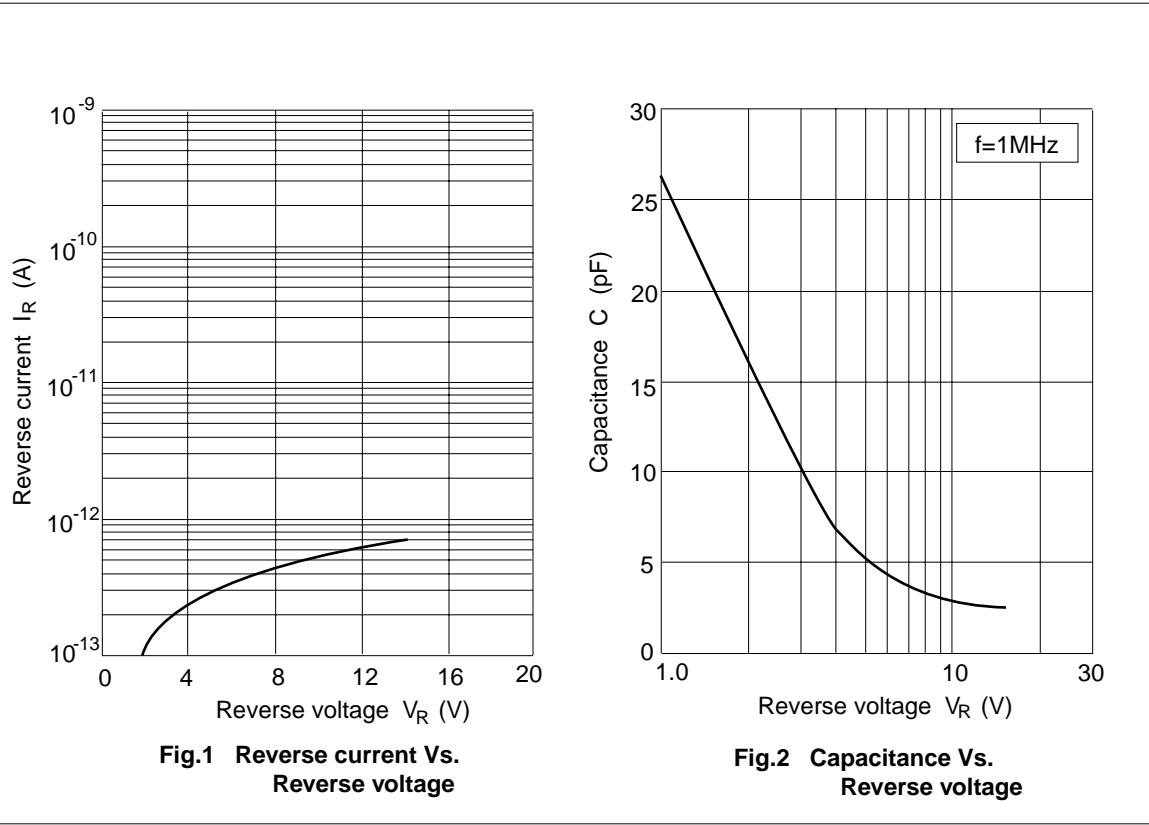
Item	Symbol	Value	Unit
Reverse voltage	$V_R$	15	V
Junction temperature	$T_j$	125	°C
Storage temperature	$T_{stg}$	-55 to +125	°C

### Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse current	$I_{R1}$	—	—	10	nA	$V_R = 10\text{ V}$
	$I_{R2}$	—	—	100		$V_R = 10\text{ V}$ , $T_a = 60\text{ °C}$
Capacitance	$C_1$	24.8	—	29.8	pF	$V_R = 1\text{ V}$ , $f = 1\text{ MHz}$
	$C_4$	6.0	—	8.3		$V_R = 4\text{ V}$ , $f = 1\text{ MHz}$
Capacitance ratio	n	3.0	—	—	—	$C_1 / C_4$
Series resistance	$r_s$	—	—	1.5	$\Omega$	$V_R = 4\text{ V}$ , $f = 100\text{ MHz}$
ESD-Capability	—	80	—	—	V	* $C = 200\text{ pF}$ , Both forward and reverse direction 1 pulse.

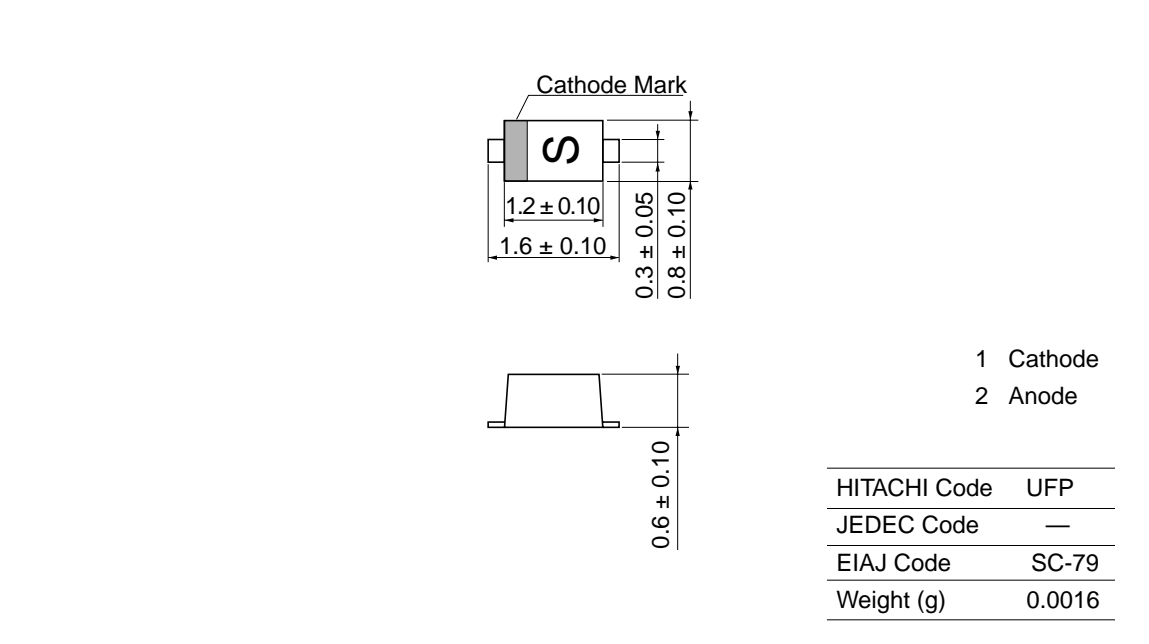
\* Failure criterion ;  $I_R \geq 20\text{ nA}$  at  $V_R = 10\text{ V}$

## HVC359



### Package Dimensions

Unit: mm



# HVC365

## Variable Capacitance Diode for VCXO

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Rev. 0  
Jan. 1996

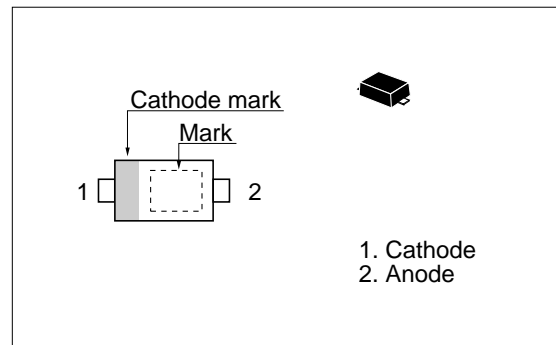
### Features

- High capacitance ratio and good C-V linearity.
- To be usable at low voltage.
- Ultra small Flat Package (UFP) is suitable for surface mount design.

### Ordering Information

Type No.	Laser Mark	Package Code
HVC365	V6	UFP

### Outline



### Absolute Maximum Ratings (Ta = 25°C)

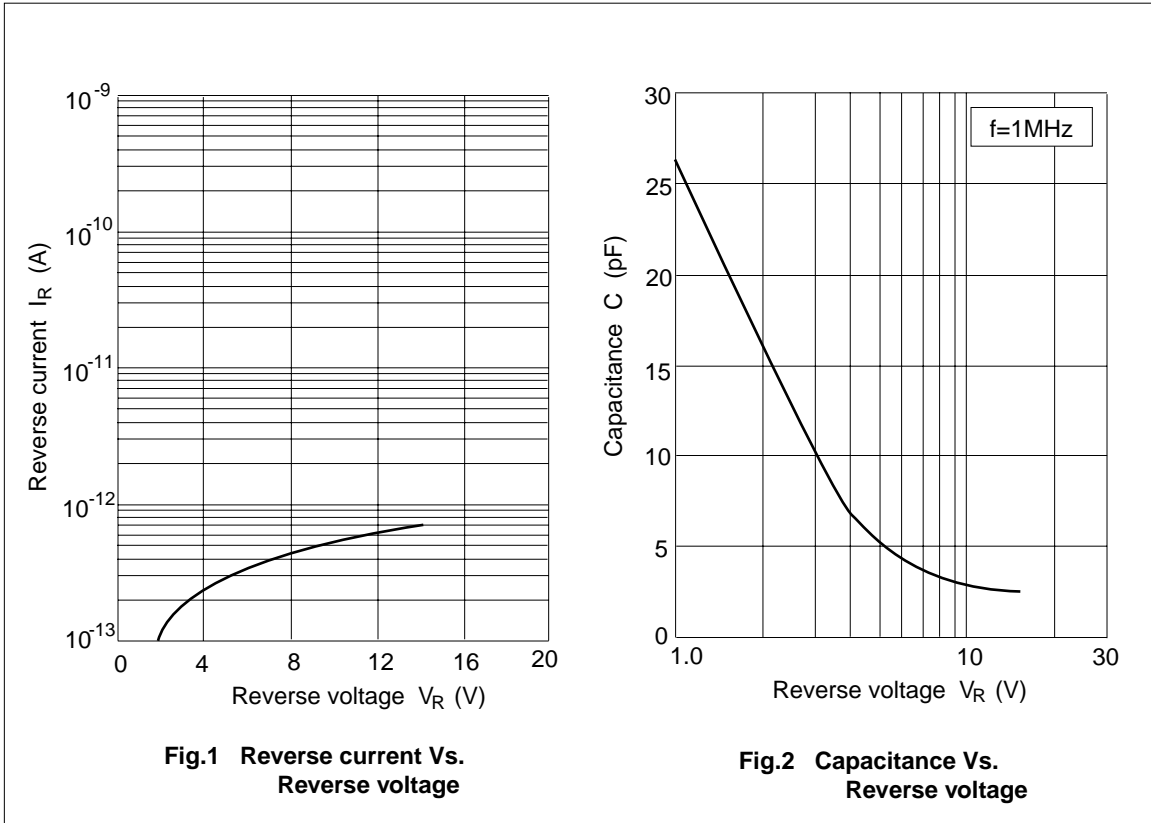
Item	Symbol	Value	Unit
Reverse voltage	$V_R$	15	V
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### Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse current	$I_{R1}$	—	—	10	nA	$V_R = 10\text{ V}$
	$I_{R2}$	—	—	100		$V_R = 10\text{ V}$ , $T_a = 60\text{ °C}$
Capacitance	$C_1$	27.05	—	28.55	pF	$V_R = 1\text{ V}$ , $f = 1\text{ MHz}$
	$C_4$	6.05	—	7.55		$V_R = 4\text{ V}$ , $f = 1\text{ MHz}$
Capacitance ratio	n	3.0	—	—	—	$C_1 / C_4$
Series resistance	$r_s$	—	—	1.5	$\Omega$	$V_R = 4\text{ V}$ , $f = 100\text{ MHz}$
ESD-Capability	—	80	—	—	V	* $C = 200\text{ pF}$ , Both forward and reverse direction 1 pulse.

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## Package Dimensions

Unit: mm

